

# MA721WA, MA721WK

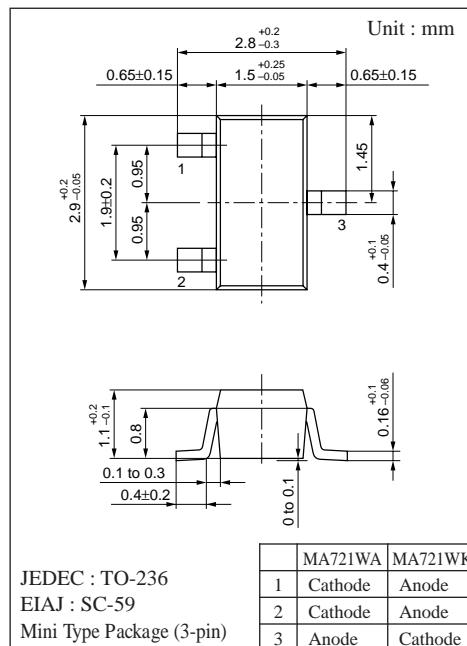
## Silicon epitaxial planer type

For super high-speed switching circuit

For small current rectification

### ■ Features

- Two elements are incorporated in MA721
- Rectification with  $I_{F(AV)} = 200\text{mA}$  (single value) possible



	MA721WA	MA721WK
1	Cathode	Anode
2	Cathode	Anode
3	Anode	Cathode

### ■ Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	30	V
Repetitive peak reverse voltage	$V_{RRM}$	30	V
Peak forward current	$I_{FM}$	300	mA
Double	$I_{FM}$	220* <sup>1</sup>	
Average forward current	$I_{F(AV)}$	200	mA
Double	$I_{F(AV)}$	130* <sup>1</sup>	
Non-repetitive peak forward surge current	$I_{FSM}^{*2}$	1	A
Double	$I_{FSM}^{*2}$	0.7* <sup>1</sup>	
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

\*<sup>1</sup> Use value per chip

\*<sup>2</sup> 50Hz sine wave, one-cycle wave, high value (non-repetitive)

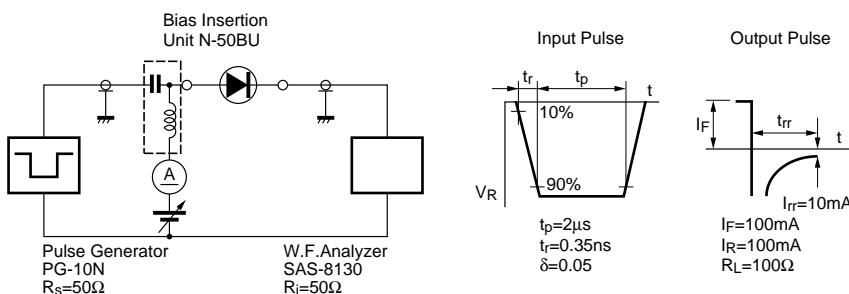
### ■ Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	$I_R$	$V_R = 30\text{V}$			50	μA
Forward voltage (DC)	$V_F$	$I_F = 200\text{mA}$			0.55	V
Terminal capacitance	$C_t$	$V_R = 0\text{V}, f=1\text{MHz}$		30		pF
Reverse recovery time	$t_{rr}^*$	$I_F = I_R = 100\text{mA}$ $I_R = 10\text{mA}, R_L = 100\Omega$		3		ns

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

2. Rated input/output frequency : 1000MHz

3. \*  $t_{rr}$  measuring circuit



### ■ Marking

Part Number	MA721WA	MA721WK
Symbol		

